

V62C1161024L(L)

Ultra Low Power 64K x 16 CMOS SRAM

Features

- Ultra Low-power consumption
 - Active: $30mA\ I_{CC}$ at 70ns
 - Stand-by: 5 µA (CMOS input/output)

1 µA (CMOS input/output, L version)

- 70/85/100/120 ns access time
- Equal access and cycle time
- Single +1.8V to 2.2V Power Supply
- Tri-state output
- Automatic power-down when deselected
- Multiple center power and ground pins for improved noise immunity
- Individual byte controls for both Read and Write cycles
- Available in 44 pin TSOP (II) Package

Functional Description

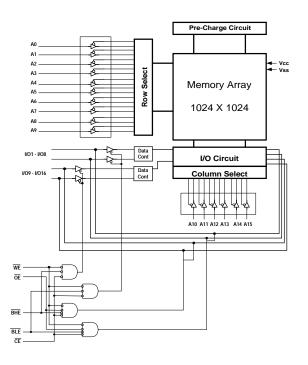
The V62C1161024L is a Low Power CMOS Static RAM organized as 65,536 words by 16 bits. Easy memory expansion is provided by an active LOW (\overline{CE}) and (\overline{OE}) pin.

This device has an automatic power-down mode feature when deselected. Separate Byte Enable controls (\overline{BLE} and \overline{BHE}) allow individual bytes to be accessed. \overline{BLE} controls the lower bits I/O1 - I/O8. \overline{BHE} controls the upper bits I/O9 - I/O16.

Writing to these devices is performed by taking Chip Enable (\overline{CE}) with Write Enable (\overline{WE}) and Byte Enable $(\overline{BLE}/\overline{BHE})$ LOW.

Reading from the device is performed by taking Chip Enable (\overline{CE}) with Output Enable (\overline{OE}) and Byte Enable ($\overline{BLE/BHE}$) LOW while Write Enable (\overline{WE}) is held HIGH.

Logic Block Diagram



TSOP(II)

		· /		1	
A4 □	1	\bigcirc	44		A 5
A3 🗀	2		43		A6
A2 □	3		42		A7
A1 □	4		41	Ī	OE
A0	5		40		BHE
CE \square	6		39		BLE
I/01 =	7		38	$\overline{}$	1/016
I/O2 =	8		37	=	I/O15
I/O3 ==	9		36	=	1/014
I/O4 □	10		35	\equiv	1/013
Vcc =	11		34	\equiv	Vss
				\equiv	
Vss □	12		33	\vdash	Vcc
I/O5 ==	13		32		1/012
1/06 □	14		31		I/O11
I/07 \square	15		30		I/O10
I/O8 ==	16		29		1/09
WE \square	17		28		NC
A15 □	18		27		Α8
A14 🗀	19		26		A9
A13 =	20		25	=	A10
A12 =	21		24	=	A11
NC =	22		23	\equiv	NC
NC L	~~		23	一	NO



Absolute Maximum Ratings *

Parameter	Symbol	Minimum	Maximum	Unit
Voltage on Any Pin Relative to Gnd	Vt	-0.5	+4.0	V
Power Dissipation	PT	_	1.0	W
Storage Temperature (Plastic)	Tstg	-55	+150	₀ C
Temperature Under Bias	Tbias	-40	+85	₀ C

^{*} Note: Stresses greater than those listed above Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and function operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect reliability.

Truth Table

CE	OE	WE	BLE	BHE	I/O1-I/O8	I/O9-I/O16	Power	Mode
Н	Χ	Χ	Χ	Χ	High-Z	High-Z	Standby	Standby
L	L	Н	L	Н	Data Out	High-Z	Active	Low Byte Read
L	L	Н	Н	L	High-Z	Data Out	Active	High Byte Read
L	L	Н	L	L	Data Out	Data Out	Active	Word Read
L	Χ	L	L	L	Data In	Data In	Active	Word Write
L	Χ	L	L	Н	Data In	High-Z	Active	Low Byte Write
L	Χ	L	Н	L	High-Z	Data In	Active	High Byte Write
L	Н	Н	Χ	Χ	High-Z	High-Z	Active	Output Disable
L	Χ	Χ	Н	Н	High-Z	High-Z	Active	Output Disable

^{*} **Key:** X = Don't Care, L = Low, H = High

Recommended Operating Conditions ($T_A = 0^{\circ}C \text{ to } +70^{\circ}C \text{ / } -40^{\circ}C \text{ to } 85^{\circ}C^{**}$)

Parameter	Symbol	Min	Тур	Max	Unit
Supply Voltage	V _{CC}	1.8	2.0	2.2	V
Supply voltage	Gnd	0.0	0.0	0.0	V
Innut Valtage	V _{IH}	1.6	-	V _{CC} + 0.2	V
Input Voltage	V _{IL}	-0.5*	-	0.4	V

^{*} V_{IL} min = -2.0V for pulse width less than $t_{RC}/2$.

^{**} For Industrial Temperature



DC Operating Characteristics ($V_{cc} = 2V \pm 10\%$, Gnd = 0V, $T_A = 0^0 C$ to $+70^0 C$ / $-40^0 C$ to $85^0 C$)

Parameter	Crim	Tost Conditi	onc	_'	70	-85		-100		-120		Unit
r ar ameter	Sym	Test Condition	Test Conditions		Max	Min	Max	Min	Max	Min	Max	
Input Leakage Current	li _{Li}	V_{cc} = Max, V_{in} = Gnd to V_{cc}			1	-	1	-	1	-	1	μА
Output Leakage Current	II _{LO}	$\overline{CE} = V_{IH} \text{ or } V_{CC} = Max,$ $V_{OUT} = Gnd \text{ to } V_{CC}$			1	-	1	-	1	-	1	μА
Operating Power Supply Current	I _{CC}	$CE = V_{IL}$, $V_{IN} = V_{IH}$ or V_{IL} , $I_{OUT} = 0$		-	3	-	3	-	3	-	3	mA
Average Operating Current	I _{CC1}	I _{OUT} = 0mA, Min Cycle, 100% Duty		-	30	-	25	-	20	-	20	mA
	I _{CC2}	$\label{eq:center} \begin{split} & CE \leq 0.2V \\ & I_{OUT} = 0 mA, \\ & \text{Cycle Time} = 1 \mu s, \text{Duty} = 10 \end{split}$	00%	-	3	-	3	-	3	-	3	mA
Standby Power Supply Current (TTL Level)	I _{SB}	CE = V _{IH}		-	0.5	-	0.5	-	0.5	-	0.5	mA
Standby Power Supply	I _{SB1}	$\overline{CE} \ge V_{CC} - 0.2V$	L	-	5	-	5	-	5	-	5	μΑ
Current (CMOS Level)		$V_{IN} \le 0.2V$ or $V_{IN} \ge V_{CC}^- 0.2V$	LL	-	1	-	1	-	1	-	1	μА
Output Low Voltage	V _{OL}	I _{OL} = 2 mA		-	0.4	-	0.4	-	0.4	-	0.4	V
Output High Voltage	V _{OH}	I _{OH} = -1 mA		1.6	-	1.6	-	1.6	-	1.6	-	V

Capacitance (f = 1MHz, $T_A = 25^0$ C)

Parameter*	Symbol	Test Condition	Max	Unit
Input Capacitance	C _{in}	$V_{in} = 0V$	7	pF
I/O Capacitance	C _{I/O}	$V_{in} = V_{out} = 0V$	8	pF

^{*} This parameter is guaranteed by device characterization and is not production tested.

AC Test Conditions

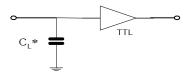
Input Pulse Level 0.4V to 1.6V Input Rise and Fall Time 5ns

Input and Output Timing 1.0V Reference Level

Output Load Condition

70ns/85ns

 $C_L = 30pf + 1TTL Load$ $C_L = 100pf + 1TTL Load$ Load for 100ns/120ns



* Including Scope and Jig Capacitance Figure A.



$\pmb{Read \ Cycle}^{\ (9)} \ (V_{cc} = 2V \underline{+} 0.2V, \ Gnd = 0V, \ T_A = 0^0C \ to \ +70^0C \ / \ -40^0C \ to \ +85^0C)$

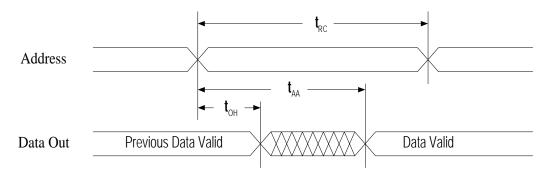
Parameter	Sym	-70		-85		-100		-120		Unit	Note
		Min	Max	Min	Max	Min	Max	Min	Max		
Read Cycle Time	t_{RC}	70	,	85	1	100	-	120	1	ns	
Address Access Time	t _{AA}	-	70	-	85	-	100	-	120	ns	
Chip Enable Access Time	t _{ACE}	-	70	-	85	-	100	-	120	ns	
Output Enable Access Time	t _{OE}	-	40	-	40	-	50	-	60	ns	
Output Hold from Address Change	t _{OH}	10	1	10	-	10	-	10	-	ns	
Chip Enable to Output in Low-Z	t _{LZ}	10		10	-	10	-	10	-	ns	4,5
Chip Disable to Output in High-Z	t _{HZ}	-	30	-	35	-	40	-	40	ns	3,4,5
Output Enable to Output in Low-Z	t _{OLZ}	5	1	5	-	5	-	5	-	ns	
Output Disable to Output in High-Z	t _{OHZ}	-	25	-	30	-	35	-	40	ns	
BLE, BHE Enable to Output in Low-Z	t _{BLZ}	5		5	-	5	-	5	-	ns	4,5
BLE, BHE Disable to Output in High-Z	t _{BHZ}	-	25	1	30	-	35	-	40	ns	3,4,5
BLE, BHE Access Time	t _{BA}	-	40	-	40	-	50	-	60	ns	

$\textbf{Write Cycle} \ ^{(11)} \ (V_{cc} = 2V \underline{+} 0.2V, \ Gnd = 0V, \ T_A = 0^0C \ to \ +70^0C \ / \ -40^0C \ to \ +85^0C)$

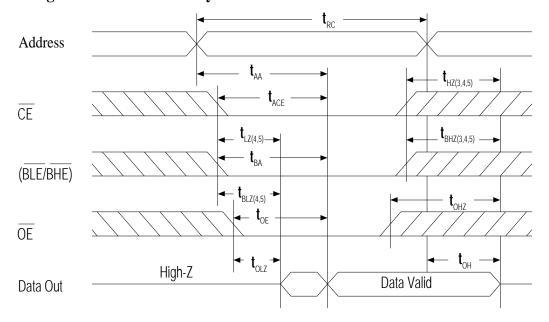
Parameter	Symbol		70	-8	5	-1	.00	-1	20	Unit	Note
		Min	Max	Min	Max	Min	Max	Min	Max		
Write Cycle Time	t _{WC}	70	-	85	-	100	-	120	-	ns	
Chip Enable to Write End	t _{CW}	60	-	70	-	80	-	90	-	ns	
Address Setup to Write End	t _{AW}	60	-	70	-	80	-	40	-	ns	
Address Setup Time	t _{AS}	0	-	0	-	0	-	0	-	ns	
Write Pulse Width	t _{WP}	50	-	60	-	70	-	80	-	ns	
Write Recovery Time	t _{WR}	0	-	0	-	0	-	0	-	ns	
Data Valid to Write End	t _{DW}	30	-	35	-	40	-	45	-	ns	
Data Hold Time	t _{DH}	0	-	0	-	0	-	0	-	ns	
Write Enable to Output in High-Z	t _{WHZ}	-	30	-	35	-	40	-	40	ns	
Output Active from Write End	tow	5	-	5	-	5	-	5	-	ns	
BLE, BHE Setup to Write End	t _{BW}	60	-	70	-	80	-	90	-	ns	



Timing Waveform of Read Cycle 1 (Address Controlled)



Timing Waveform of Read Cycle 2

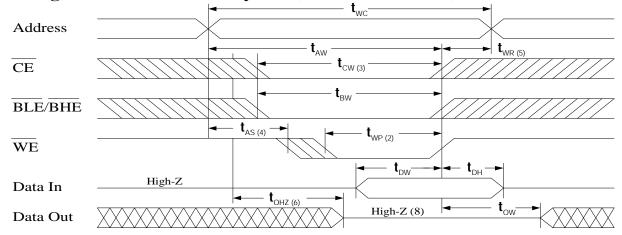


Notes (Read Cycle)

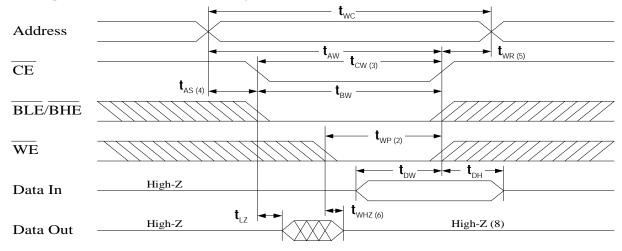
- 1. WE are high for read cycle.
- 2. All read cycle timing is referenced from the last valid address to the first transition address.
- 3. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit condition referenced to V_{OH} or V_{OL} levels.
- 4. At any given temperature and voltage condition t_{HZ} (max.) is less than t_{LZ} (min.) both for a given device and from device to device.
- 5. Transition is measured \pm 200mV from steady state voltage with load. This parameter is sampled and not 100% tested.
- 6. Device is continuously selected with $\overline{CE} = V_{IL}$.
- 7. Address valid prior to coincident with $\overline{\text{CE}}$ transition Low.
- 8. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.
- 9. For test conditions, see AC Test Condition, Figure A.



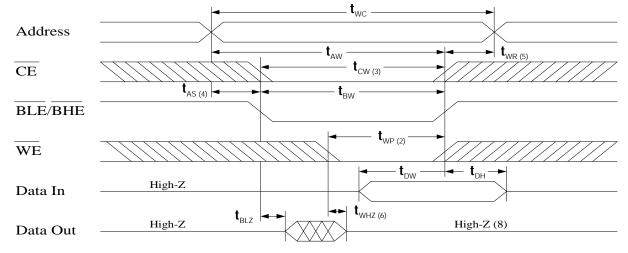
Timing Waveform of Write Cycle 1 (Address Controlled)



Timing Waveform of Write Cycle 2 (CE Controlled)



Timing Waveform of Write Cycle 3 (BLE/BHE Controlled)



V62C1161024L(L)



Notes (Write Cycle)

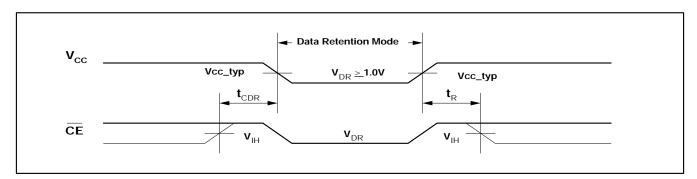
- 1. All write timing is referenced from the last valid address to the first transition address.
- 2. A write occurs during the overlap of a low \overline{CE} and \overline{WE} . A write begins at the latest transition among \overline{CE} and \overline{WE} going low: A write ends at the earliest transition among \overline{CE} going high and \overline{WE} going high. t_{WP} is measured from the beginning of write to the end of write.
- 3. t_{cw} is measured from the later of \overline{CE} going low to end of write.
- 4. t_{AS} is measured from the address valid to the beginning of write.
- 5. t_{WR} is measured from the end of write to the address change.
- 6. If \overline{OE} , \overline{CE} and \overline{WE} are in the Read Mode during this period, the I/O pins are in the output Low-Z state. Inputs of opposite phase of the output must not be applied because bus contention can occur.
- For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.
- 8. If $\overline{\text{CE}}$ goes low simultaneously with $\overline{\text{WE}}$ going low or after $\overline{\text{WE}}$ going low, the outputs remain high impedance state.
- 9. Dout is the read data of the new address.
- 10. When $\overline{\text{CE}}$ is low: I/O pins are in the outputs state. The input signals in the opposite phase leading to the output should not be applied.
- 11. For test conditions, see AC Test Condition, Figure A & B.



Data Retention Characteristics (L Version Only)(1)

Parameter	Symbol	Test Condition	Min	Max	Unit
V _{CC} for Data Retention	V _{DR}	$\overline{\text{CE}} \ge V_{\text{CC}} - 0.2V$	1.0	-	V
Data Retention Current	I _{CCDR}	L	-	5 1	μА
Chip Deselect to Data Retention Time	t _{CDR}	$V_{IN} \supseteq V_{CC}$ - 0.2V or	0	-	ns
Operation Recovery Time ⁽²⁾	t _R	$V_{IN} \leq 0.2V$	t _{RC}	-	ns

Data Retention Waveform (L Version Only) ($T_A = 0^0$ C to $+70^0$ C / -40^0 C to $+85^0$ C)



Notes

- 1. L-version includes this feature.
- 2. This Parameter is sampled and not 100% tested.
- 3. For test conditions, see AC Test Condition, Figure A.
- 4. This parameter is tested with CL = 5pF as shown in Figure B. Transition is measured $\pm 500mV$ from steady-state voltage.
- 5. This parameter is guaranteed, but is not tested.
- 6. $\overline{\text{WE}}$ is High for read cycle.
- 7. $\overline{\text{CE}}$ and $\overline{\text{OE}}$ are LOW for read cycle.
- 8. Address valid prior to or coincident with $\overline{\text{CE}}$ transition LOW.
- 9. All read cycle timings are referenced from the last valid address to the first transtion address.
- 10. CE or WE must be HIGH during address transition.
- 11. All write cycle timings are referenced from the last valid address to the first transition address.



Ordering Information

Device Type*	Speed	Package
V62C1161024L-70T	70 ns	44-pin TSOP Type 2
V62C1161024L-85T	85 ns	
V62C1161024L-100T	100 ns	
V62C1161024L-120T	120 ns	
V62C1161024LL-70T	70 ns	
V62C1161024LL-85T	85 ns	
V62C1161024LL-100T	100 ns	
V62C1161024LL-120T	120 ns	

^{*} For Industrial temperature tested devices, an "I" designator will be added to the end of the device number.

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